

# NTMFS4927N, NTMFS4927NC

## MOSFET – Power, Single, N-Channel, SO-8 FL 30 V, 38 A

### Features

- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Optimized for 5 V, 12 V Gate Drives
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- CPU Power Delivery
- DC-DC Converters

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

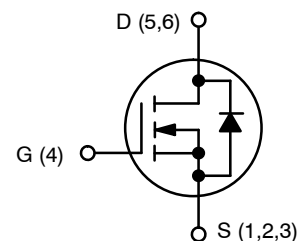
| Parameter                                                 |                                               |                        | Symbol                            | Value       | Unit |
|-----------------------------------------------------------|-----------------------------------------------|------------------------|-----------------------------------|-------------|------|
| Drain-to-Source Voltage                                   |                                               |                        | V <sub>DSS</sub>                  | 30          | V    |
| Gate-to-Source Voltage                                    |                                               |                        | V <sub>GS</sub>                   | ±20         | V    |
| Continuous Drain Current R <sub>θJA</sub> (Note 1)        | Steady State                                  | T <sub>A</sub> = 25°C  | I <sub>D</sub>                    | 13.6        | A    |
|                                                           |                                               | T <sub>A</sub> = 100°C |                                   | 8.6         |      |
| Power Dissipation R <sub>θJA</sub> (Note 1)               |                                               | T <sub>A</sub> = 25°C  | P <sub>D</sub>                    | 2.70        | W    |
| Continuous Drain Current R <sub>θJA</sub> ≤ 10 s (Note 1) |                                               | T <sub>A</sub> = 25°C  | I <sub>D</sub>                    | 20.4        | A    |
|                                                           |                                               | T <sub>A</sub> = 100°C |                                   | 12.9        |      |
| Power Dissipation R <sub>θJA</sub> ≤ 10 s (Note 1)        |                                               | T <sub>A</sub> = 25°C  | P <sub>D</sub>                    | 6.04        | W    |
| Continuous Drain Current R <sub>θJA</sub> (Note 2)        |                                               | T <sub>A</sub> = 25°C  | I <sub>D</sub>                    | 7.9         | A    |
|                                                           |                                               | T <sub>A</sub> = 100°C |                                   | 5.0         |      |
| Power Dissipation R <sub>θJA</sub> (Note 2)               |                                               | T <sub>A</sub> = 25°C  | P <sub>D</sub>                    | 0.92        | W    |
| Continuous Drain Current R <sub>θJC</sub> (Note 1)        |                                               | T <sub>C</sub> = 25°C  | I <sub>D</sub>                    | 38          | A    |
|                                                           |                                               | T <sub>C</sub> = 100°C |                                   | 24          |      |
| Power Dissipation R <sub>θJC</sub> (Note 1)               |                                               | T <sub>C</sub> = 25°C  | P <sub>D</sub>                    | 20.8        | W    |
| Pulsed Drain Current                                      | T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs |                        | I <sub>DM</sub>                   | 160         | A    |
| Current Limited by Package                                |                                               | T <sub>A</sub> = 25°C  | I <sub>Dmax</sub>                 | 100         | A    |
| Operating Junction and Storage Temperature                |                                               |                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |
| Source Current (Body Diode)                               |                                               |                        | I <sub>S</sub>                    | 21          | A    |
| Drain to Source DV/DT                                     |                                               |                        | dV/d <sub>t</sub>                 | 6.0         | V/ns |



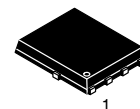
ON Semiconductor®

<http://onsemi.com>

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ MAX        | $I_D$ MAX |
|---------------|-------------------------|-----------|
| 30 V          | 7.3 m $\Omega$ @ 10 V   | 38 A      |
|               | 12.0 m $\Omega$ @ 4.5 V |           |

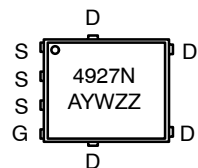


N-CHANNEL MOSFET



SO-8 FLAT LEAD  
CASE 488AA  
STYLE 1

### MARKING DIAGRAM



4927N = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

| Device         | Package              | Shipping†             |
|----------------|----------------------|-----------------------|
| NTMFS4927NT1G  | SO-8 FL<br>(Pb-Free) | 1500 /<br>Tape & Reel |
| NTMFS4927NCT1G |                      |                       |
| NTMFS4927NT3G  | SO-8 FL<br>(Pb-Free) | 5000 /<br>Tape & Reel |
| NTMFS4927NCT3G |                      |                       |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTMFS4927N, NTMFS4927NC

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

| Parameter                                                                                                                                                                                      | Symbol          | Value | Unit |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------|-------|------|
| Single Pulse Drain-to-Source Avalanche Energy (T <sub>J</sub> = 25°C, V <sub>DD</sub> = 24 V, V <sub>GS</sub> = 20 V, I <sub>L</sub> = 20 A <sub>pk</sub> , L = 0.1 mH, R <sub>G</sub> = 25 Ω) | E <sub>AS</sub> | 20    | mJ   |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                                                                                                                              | T <sub>L</sub>  | 260   | °C   |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

## THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol           | Value | Unit |
|---------------------------------------------|------------------|-------|------|
| Junction-to-Case (Drain)                    | R <sub>θJC</sub> | 6.0   | °C/W |
| Junction-to-Ambient – Steady State (Note 3) | R <sub>θJA</sub> | 46.3  |      |
| Junction-to-Ambient – Steady State (Note 4) | R <sub>θJA</sub> | 136.2 |      |
| Junction-to-Ambient – (t ≤ 10 s) (Note 3)   | R <sub>θJA</sub> | 20.7  |      |

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
4. Surface-mounted on FR4 board using the minimum recommended pad size.

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

| Parameter                                                 | Symbol                               | Test Condition                                                                                                 | Min | Typ | Max  | Unit  |
|-----------------------------------------------------------|--------------------------------------|----------------------------------------------------------------------------------------------------------------|-----|-----|------|-------|
| <b>OFF CHARACTERISTICS</b>                                |                                      |                                                                                                                |     |     |      |       |
| Drain-to-Source Breakdown Voltage                         | V <sub>(BR)DSS</sub>                 | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                 | 30  |     |      | V     |
| Drain-to-Source Breakdown Voltage (transient)             | V <sub>(BR)DSSst</sub>               | V <sub>GS</sub> = 0 V, I <sub>D(aval)</sub> = 8.4 A, T <sub>case</sub> = 25°C, t <sub>transient</sub> = 100 ns | 34  |     |      | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V <sub>(BR)DSS</sub> /T <sub>J</sub> |                                                                                                                |     | 24  |      | mV/°C |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                     | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V                                                                  |     |     | 1.0  | μA    |
|                                                           |                                      |                                                                                                                |     |     | 10   |       |
| Gate-to-Source Leakage Current                            | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V                                                                 |     |     | ±100 | nA    |

## ON CHARACTERISTICS (Note 5)

|                                            |                                     |                                                             |                       |     |     |       |
|--------------------------------------------|-------------------------------------|-------------------------------------------------------------|-----------------------|-----|-----|-------|
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub>                 | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA | 1.32                  | 1.6 | 2.2 | V     |
| Negative Threshold Temperature Coefficient | V <sub>GS(TH)</sub> /T <sub>J</sub> |                                                             |                       | 3.7 |     | mV/°C |
| Drain-to-Source On Resistance              | R <sub>DS(on)</sub>                 | V <sub>GS</sub> = 10 V                                      | I <sub>D</sub> = 30 A | 5.8 | 7.3 | mΩ    |
|                                            |                                     |                                                             |                       | 5.7 |     |       |
|                                            |                                     | V <sub>GS</sub> = 4.5 V                                     | I <sub>D</sub> = 30 A | 9.6 | 12  |       |
|                                            |                                     |                                                             | I <sub>D</sub> = 15 A | 9.2 |     |       |
| Forward Transconductance                   | g <sub>FS</sub>                     | V <sub>DS</sub> = 1.5 V, I <sub>D</sub> = 15 A              |                       | 40  |     | S     |

## CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |                                     |                                                          |  |       |       |    |
|------------------------------|-------------------------------------|----------------------------------------------------------|--|-------|-------|----|
| Input Capacitance            | C <sub>ISS</sub>                    | V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 15 V |  | 913   |       | pF |
| Output Capacitance           | C <sub>OSS</sub>                    |                                                          |  | 366   |       |    |
| Reverse Transfer Capacitance | C <sub>RSS</sub>                    |                                                          |  | 108   |       |    |
| Capacitance Ratio            | C <sub>RSS</sub> / C <sub>ISS</sub> | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 15 V, f = 1 MHz |  | 0.118 | 0.237 |    |

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

# NTMFS4927N, NTMFS4927NC

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                       |              |                                                                  |  |      |  |    |
|-----------------------|--------------|------------------------------------------------------------------|--|------|--|----|
| Total Gate Charge     | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$ |  | 8.0  |  | nC |
| Threshold Gate Charge | $Q_{G(TH)}$  |                                                                  |  | 1.6  |  |    |
| Gate-to-Source Charge | $Q_{GS}$     |                                                                  |  | 3.1  |  |    |
| Gate-to-Drain Charge  | $Q_{GD}$     |                                                                  |  | 3.1  |  |    |
| Total Gate Charge     | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$  |  | 16.0 |  | nC |

### SWITCHING CHARACTERISTICS (Note 6)

|                     |              |                                                                                     |  |      |  |    |
|---------------------|--------------|-------------------------------------------------------------------------------------|--|------|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$ |  | 9.2  |  | ns |
| Rise Time           | $t_r$        |                                                                                     |  | 25.5 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                     |  | 14.0 |  |    |
| Fall Time           | $t_f$        |                                                                                     |  | 4.4  |  |    |
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\ \Omega$  |  | 6.5  |  | ns |
| Rise Time           | $t_r$        |                                                                                     |  | 21.0 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                     |  | 18.0 |  |    |
| Fall Time           | $t_f$        |                                                                                     |  | 3.0  |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                              |                           |      |      |     |   |
|-------------------------|----------|------------------------------------------------------------------------------|---------------------------|------|------|-----|---|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 30\text{ A}$                                     | $T_J = 25^\circ\text{C}$  |      | 0.87 | 1.1 | V |
|                         |          |                                                                              | $T_J = 125^\circ\text{C}$ |      | 0.76 |     |   |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 30\text{ A}$ |                           | 21.4 |      | ns  |   |
| Charge Time             | $t_a$    |                                                                              |                           | 10.5 |      |     |   |
| Discharge Time          | $t_b$    |                                                                              |                           | 10.9 |      |     |   |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                              |                           | 8.4  |      | nC  |   |

### PACKAGE PARASITIC VALUES

|                   |       |                          |  |       |     |          |
|-------------------|-------|--------------------------|--|-------|-----|----------|
| Source Inductance | $L_S$ | $T_A = 25^\circ\text{C}$ |  | 1.00  |     | nH       |
| Drain Inductance  | $L_D$ |                          |  | 0.005 |     | nH       |
| Gate Inductance   | $L_G$ |                          |  | 1.84  |     | nH       |
| Gate Resistance   | $R_G$ |                          |  | 0.90  | 2.2 | $\Omega$ |

5. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

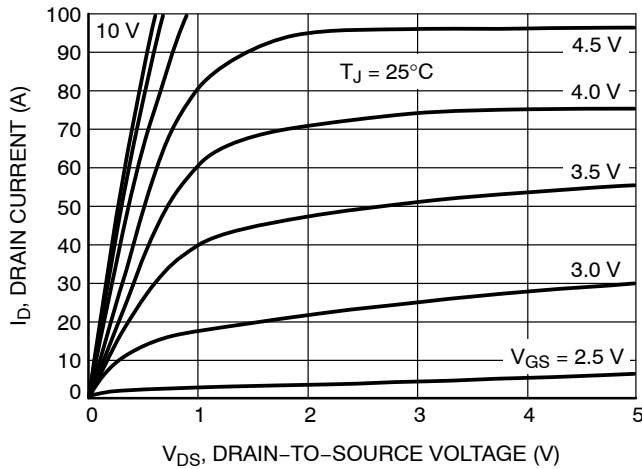


Figure 1. On-Region Characteristics

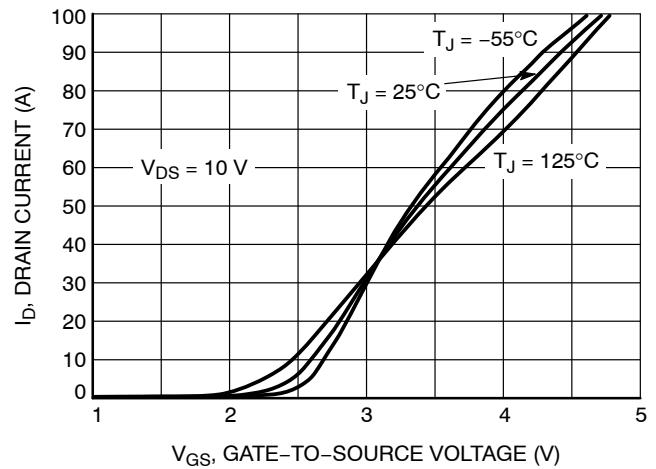


Figure 2. Transfer Characteristics

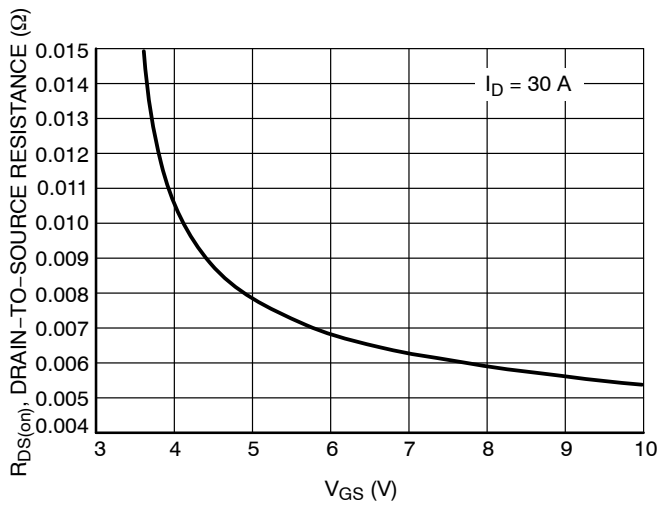


Figure 3. On-Resistance vs.  $V_{GS}$

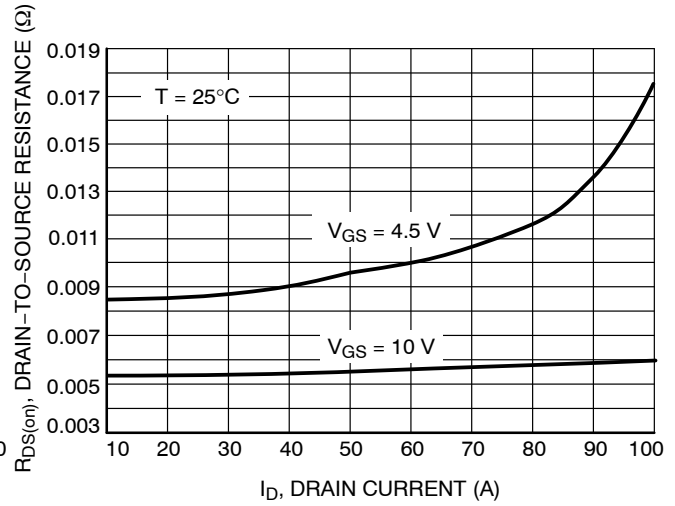


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

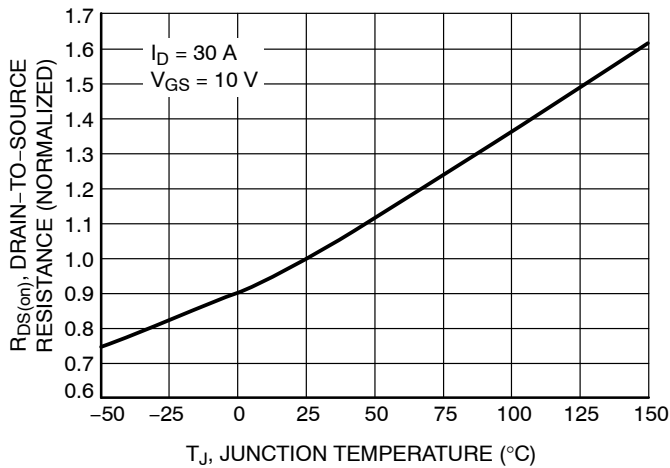


Figure 5. On-Resistance Variation with Temperature

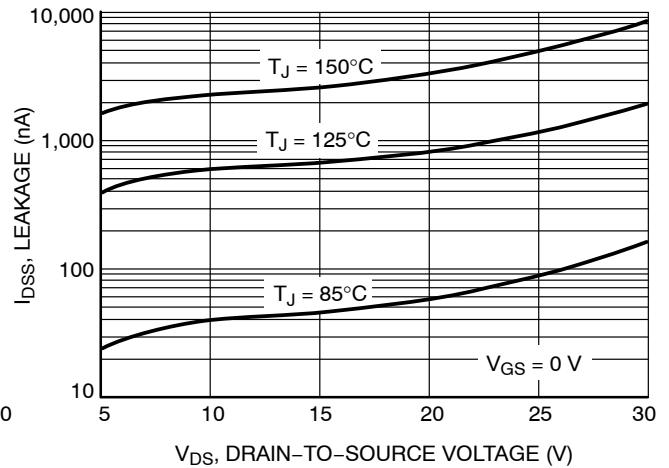


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

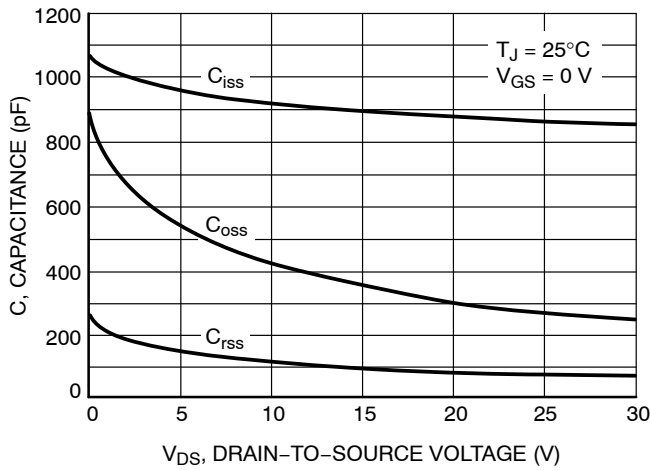


Figure 7. Capacitance Variation

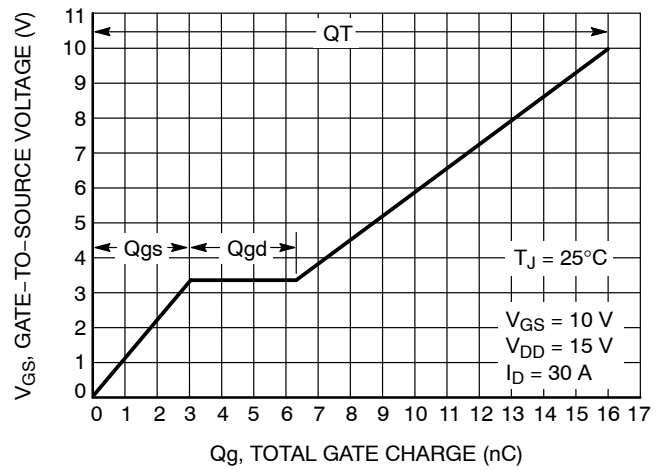


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

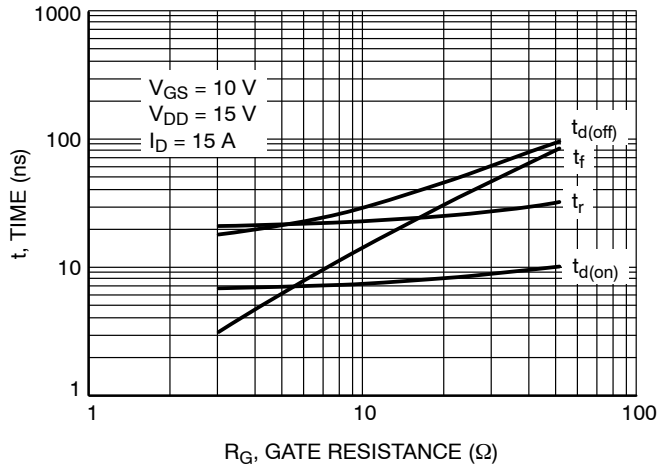


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

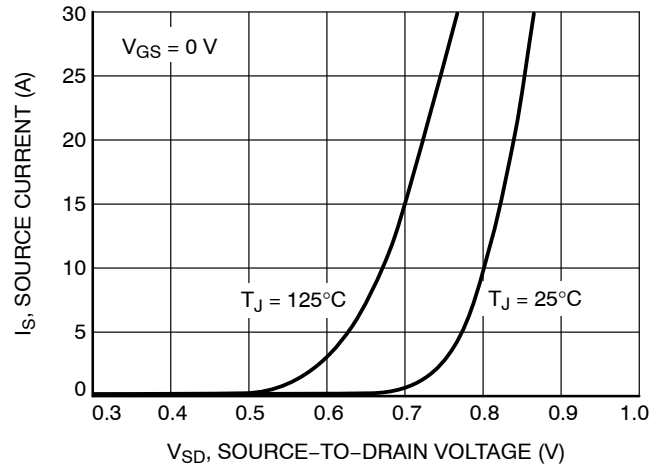


Figure 10. Diode Forward Voltage vs. Current

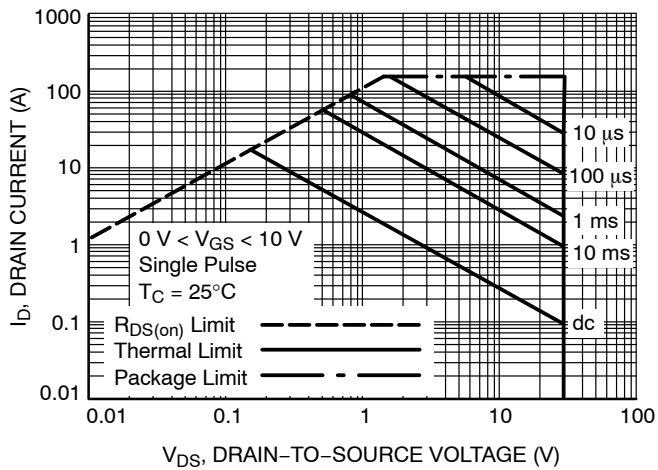


Figure 11. Maximum Rated Forward Biased Safe Operating Area

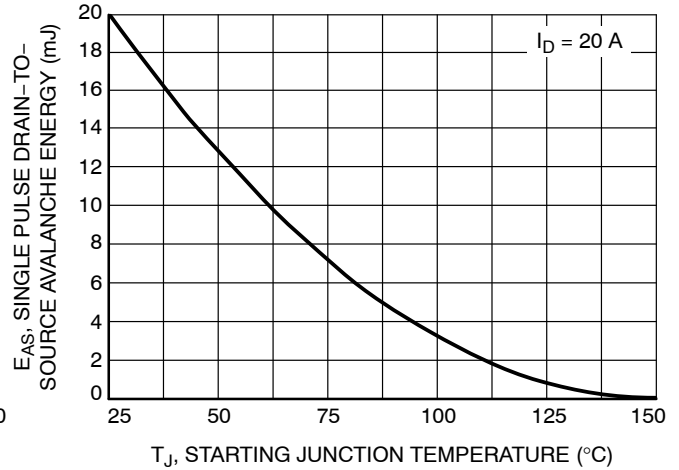
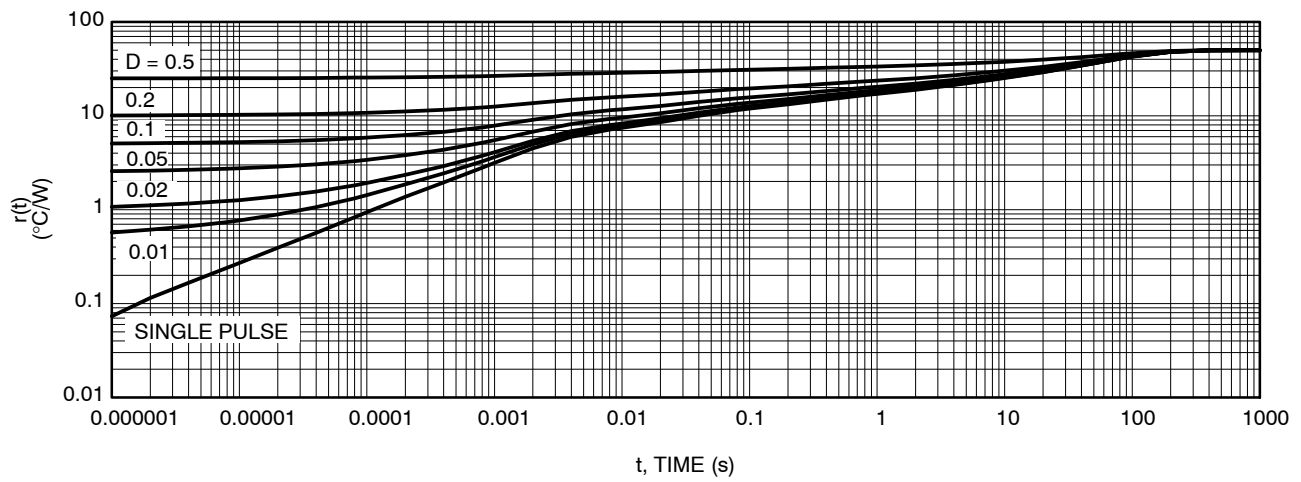


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

# NTMFS4927N, NTMFS4927NC

## TYPICAL CHARACTERISTICS





1  
SCALE 2:1

**DFN5 5x6, 1.27P**  
**(SO-8FL)**  
**CASE 488AA**  
**ISSUE N**

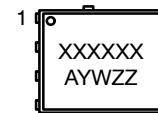
DATE 25 JUN 2018

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

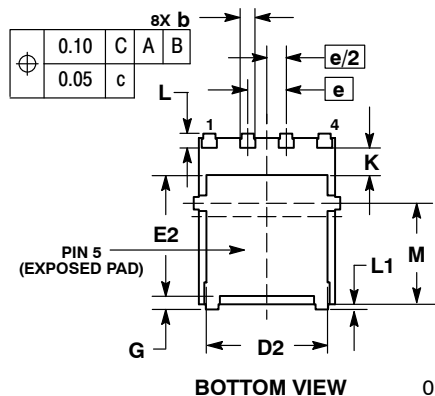
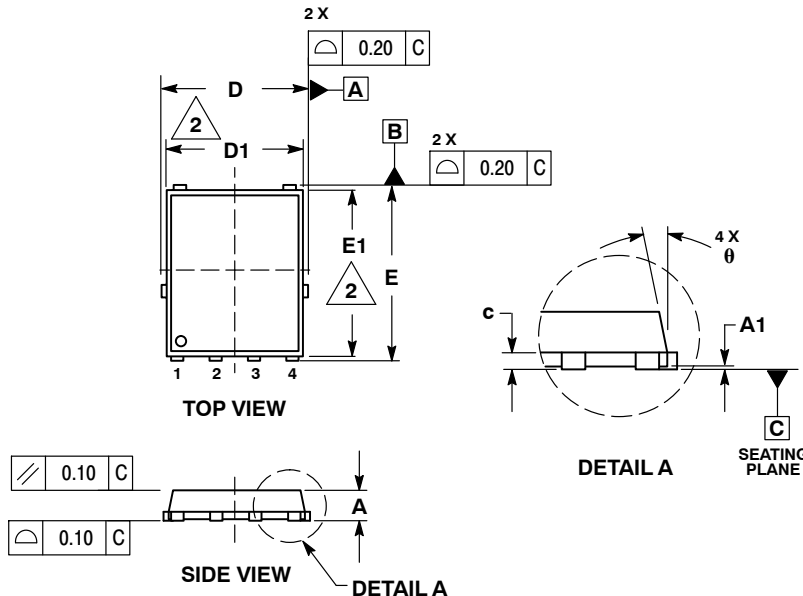
| DIM | MILLIMETERS |       |      |
|-----|-------------|-------|------|
|     | MIN         | NOM   | MAX  |
| A   | 0.90        | 1.00  | 1.10 |
| A1  | 0.00        | ---   | 0.05 |
| b   | 0.33        | 0.41  | 0.51 |
| c   | 0.23        | 0.28  | 0.33 |
| D   | 5.00        | 5.15  | 5.30 |
| D1  | 4.70        | 4.90  | 5.10 |
| D2  | 3.80        | 4.00  | 4.20 |
| E   | 6.00        | 6.15  | 6.30 |
| E1  | 5.70        | 5.90  | 6.10 |
| E2  | 3.45        | 3.65  | 3.85 |
| e   | 1.27 BSC    |       |      |
| G   | 0.51        | 0.575 | 0.71 |
| K   | 1.20        | 1.35  | 1.50 |
| L   | 0.51        | 0.575 | 0.71 |
| L1  | 0.125 REF   |       |      |
| M   | 3.00        | 3.40  | 3.80 |
| θ   | 0°          | ---   | 12°  |

**GENERIC**  
**MARKING DIAGRAM\***

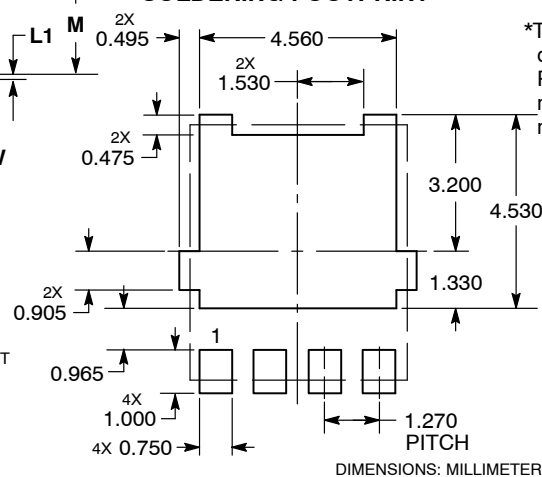


XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



**RECOMMENDED**  
**SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

STYLE 2:  
PIN 1. ANODE  
2. ANODE  
3. ANODE  
4. NO CONNECT  
5. CATHODE

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

|                         |                                 |                                                                                                                                                                                  |
|-------------------------|---------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <b>DOCUMENT NUMBER:</b> | <b>98AON14036D</b>              | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| <b>DESCRIPTION:</b>     | <b>DFN5 5x6, 1.27P (SO-8FL)</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                               |

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